

Characteristics (T_j = 25°C)
Kennwerte (T_j = 25°C)

			Min.	Typ.	Max.
DC current gain – Kollektor-Basis-Stromverhältnis					
- I _C = 0.1 mA, - V _{CE} = 10 V	PZT2907	h _{FE}	35	–	–
	PZT2907A	h _{FE}	75	–	–
- I _C = 1 mA, - V _{CE} = 10 V	PZT2907	h _{FE}	50	–	–
	PZT2907A	h _{FE}	100	–	–
- I _C = 10 mA, - V _{CE} = 10 V	PZT2907	h _{FE}	75	–	–
	PZT2907A	h _{FE}	100	–	–
- I _C = 150 mA, - V _{CE} = 10 V	PZT2907	h _{FE}	100	–	300
	PZT2907A	h _{FE}	100	–	300
- I _C = 500 mA, - V _{CE} = 10 V	PZT2907	h _{FE}	30	–	–
	PZT2907A	h _{FE}	50	–	–
Gain-Bandwidth Product – Transitfrequenz					
- I _C = 20 mA, - V _{CE} = 20 V, f = 100 MHz		f _T	200 MHz	–	–
Collector-Base Capacitance – Kollektor-Basis-Kapazität					
- V _{CB} = 10 V, I _E = i _e = 0, f = 1 MHz		C _{CBO}	–	–	8 pF
Emitter-Base Capacitance – Emitter-Basis-Kapazität					
- V _{EB} = 0.5 V, I _C = i _c = 0, f = 1 MHz		C _{EBO}	–	–	30 pF
Switching times – Schaltzeiten					
delay time	- V _{CC} = 30 V, - I _C = 150 mA,	t _d	–	–	10
rise time	- I _{B1} = 15 mA	t _r	–	–	40
storage time	- V _{CC} = 6 V, - I _C = 150 mA,	t _s	–	–	80
fall time	- I _{B1} = - I _{B2} = 15 mA	t _f	–	–	30
Thermal resistance junction to ambient air Wärmewiderstand Sperrschicht – umgebende Luft		R _{thA}	< 93 K/W ¹⁾		
Thermal resistance junction to soldering point Wärmewiderstand Sperrschicht – Löt看		R _{thS}	< 27 K/W		
Recommended complementary NPN transistors Empfohlene komplementäre NPN-Transistoren			PZT2222, PZT2222A		

1 Mounted on P.C. board with 3 mm² copper pad at each terminal
Montage auf Leiterplatte mit 3 mm² Kupferbelag (Löt看) an jedem Anschluss